

# 10V Drive Nch MOS FET

## RDX100N60

**●Structure**

Silicon N-channel MOS FET

**●Features**

- 1) Low on-resistance.
- 2) Low input capacitance.
- 3) Excellent resistance to damage from static electricity.

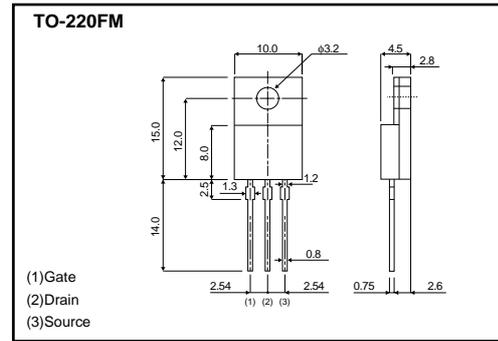
**●Applications**

Switching

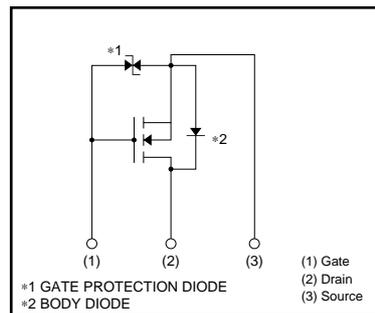
**●Packaging specifications**

Type	Package	Bulk
	Code	-
	Basic ordering unit (pieces)	500
RDX100N60		○

**●External dimensions (Unit : mm)**



**●Inner circuit**



**●Absolute maximum ratings (Ta=25°C)**

Parameter	Symbol	Limits	Unit	
Drain-source voltage	$V_{DSS}$	600	V	
Gate-source voltage	$V_{GSS}$	$\pm 30$	V	
Drain current	Continuous	$I_D$ *1	$\pm 10$	A
	Pulsed	$I_{DP}$ *2	$\pm 40$	A
Source current (Body diode)	Continuous	$I_S$	10	A
	Pulsed	$I_{SP}$ *2	40	A
Avalanche current	$I_{AS}$ *3	10	A	
Avalanche energy	$E_{AS}$ *4	230	mJ	
Total power dissipation (Tc=25°C)	$P_D$	45	W	
Channel temperature	Tch	150	°C	
Range of storage temperature	Tstg	-55 to +150	°C	

\*1 Limited only by maximum temperature allowed \*2  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$   
 \*3 L  $\approx 4.0mH$   $V_{DD}=90V$   $R_g=25\Omega$  \*4 L  $\approx 4.0mH$   $V_{DD}=90V$   $R_g=25\Omega$  starting Tch=25°C

**●Thermal resistance**

Parameter	Symbol	Limits	Unit
Channel to case	Rth(ch-c)	2.78	°C/W

## Transistors

## ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	$I_{GSS}$	–	–	±10	μA	$V_{GS} = \pm 25V, V_{DS} = 0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	600	–	–	V	$I_D = 1mA, V_{GS} = 0V$
Zero gate voltage drain current	$I_{DSS}$	–	–	25	μA	$V_{DS} = 600V, V_{GS} = 0V$
Gate threshold voltage	$V_{GS(th)}$	2.0	–	4.0	V	$V_{DS} = 10V, I_D = 1mA$
Static drain-source on-state resistance	$R_{DS(on)}^*$	–	0.48	0.65	Ω	$I_D = 5.0A, V_{GS} = 10V$
Forward transfer admittance	$ Y_{fs} ^*$	4.0	7.0	–	S	$V_{DS} = 10V, I_D = 5.0A$
Input capacitance	$C_{iss}$	–	1600	–	pF	$V_{DS} = 25V$
Output capacitance	$C_{oss}$	–	175	–	pF	$V_{GS} = 0V$
Reverse transfer capacitance	$C_{rss}$	–	30	–	pF	$f = 1MHz$
Turn-on delay time	$t_{d(on)}^*$	–	28	–	ns	$V_{DD} = 150V$
Rise time	$t_r^*$	–	23	–	ns	$I_D = 5.0A$
Turn-off delay time	$t_{d(off)}^*$	–	75	–	ns	$V_{GS} = 10V$
Fall time	$t_f^*$	–	44	–	ns	$R_L = 30\Omega$
Total gate charge	$Q_g^*$	–	45	–	nC	$V_{DD} = 300V$
Gate-source charge	$Q_{gs}^*$	–	10	–	nC	$V_{GS} = 10V$
Gate-drain charge	$Q_{gd}^*$	–	20	–	nC	$I_D = 10A$

\*Pulsed

## ●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_{SD}^*$	–	–	1.5	V	$I_S = 10A, V_{GS} = 0V$
Reverse recovery time	$t_{rr}$	–	550	–	ns	$I_{DR} = 10A, V_{GS} = 0V$
Reverse recovery charge	$Q_{rr}$	–	4.7	–	μC	$di/dt = 100A / \mu s$

\* Pulsed

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